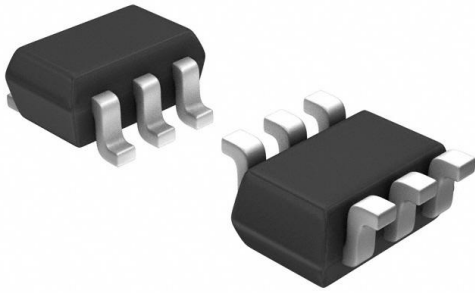


BCR129SH6327XTSA1 Datasheet

www.digi-electronics.com



<https://www.DiGi-Electronics.com>

DiGi Electronics Part Number	BCR129SH6327XTSA1-DG
Manufacturer	Infineon Technologies
Manufacturer Product Number	BCR129SH6327XTSA1
Description	TRANS 2NPN PREBIAS 0.25W SOT363
Detailed Description	Pre-Biased Bipolar Transistor (BJT) 2 NPN - Pre-Biased (Dual) 50V 100mA 150MHz 250mW Surface Mount PG-SOT363-PO



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

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Purchase and inquiry

Manufacturer Product Number:

BCR129SH6327XTSA1

Series:

-

Transistor Type:

2 NPN - Pre-Biased (Dual)

Voltage - Collector Emitter Breakdown (Max):

50V

Resistor - Emitter Base (R2):

-

Vce Saturation (Max) @ Ib, Ic:

300mV @ 500µA, 10mA

Frequency - Transition:

150MHz

Mounting Type:

Surface Mount

Supplier Device Package:

PG-SOT363-PO

Manufacturer:

Infineon Technologies

Product Status:

Obsolete

Current - Collector (Ic) (Max):

100mA

Resistor - Base (R1):

10kOhms

DC Current Gain (hFE) (Min) @ Ic, Vce:

120 @ 5mA, 5V

Current - Collector Cutoff (Max):

-

Power - Max:

250mW

Package / Case:

6-VSSOP, SC-88, SOT-363

Base Product Number:

BCR129

Environmental & Export classification

RoHS Status:

ROHS3 Compliant

REACH Status:

REACH Unaffected

HTSUS:

8541.21.0095

Moisture Sensitivity Level (MSL):

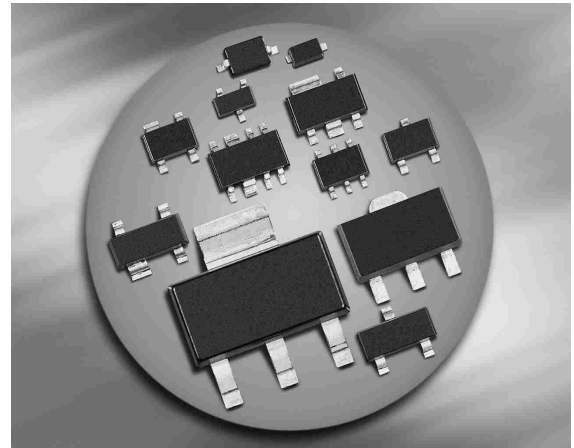
1 (Unlimited)

ECCN:

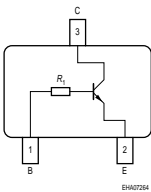
EAR99

NPN Silicon Digital Transistor

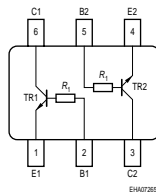
- Switching circuit, inverter, interface circuit, driver circuit
- Built in bias resistor ($R_1=10\text{ k}\Omega$)
- BCR129S: Two internally isolated transistors with good matching in one multichip package
- BCR129S: For orientation in reel see package information below
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101



BCR129 BCR129W



BCR129S



Type	Marking	Pin Configuration						Package
		1=B	2=E	3=C	-	-	-	
BCR129	WVs	1=B	2=E	3=C	-	-	-	SOT23
BCR129S	WVs	1=E1	2=B1	3=C2	4=E2	5=B2	6=C1	SOT363
BCR129W	WVs	1=B	2=E	3=C	-	-	-	SOT323



Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}	50	V
Collector-base voltage	V_{CBO}	50	
Input forward voltage	$V_{i(fwd)}$	40	
Input reverse voltage	$V_{i(rev)}$	5	
Collector current	I_C	100	mA
Total power dissipation- BCR129, $T_S \leq 102^\circ\text{C}$ BCR129S, $T_S \leq 115^\circ\text{C}$ BCR129W, $T_S \leq 124^\circ\text{C}$	P_{tot}	200 250 250	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

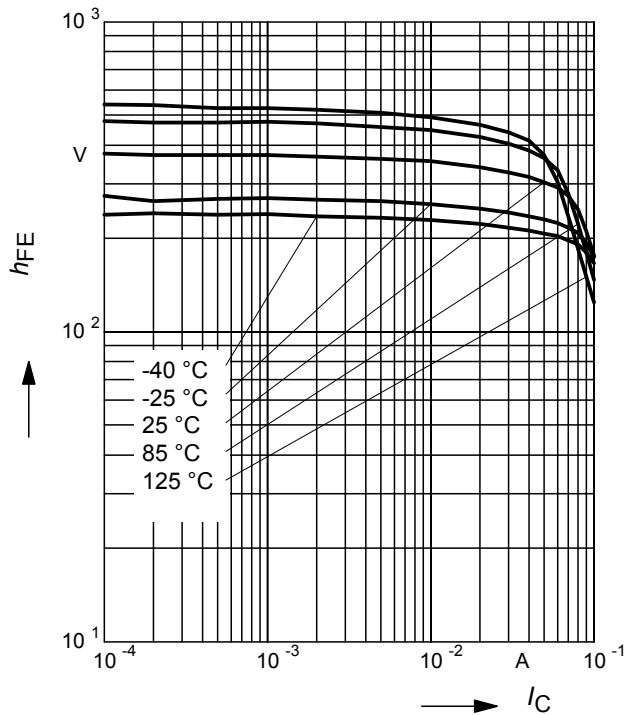
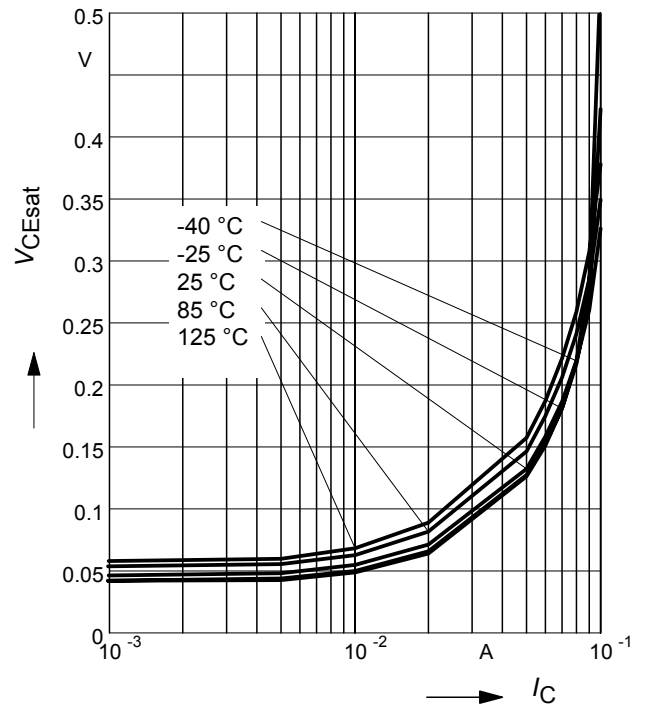
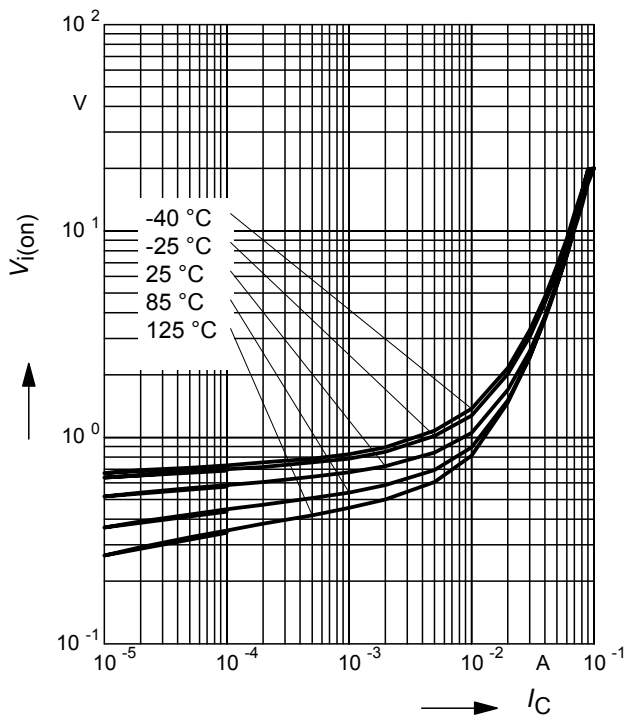
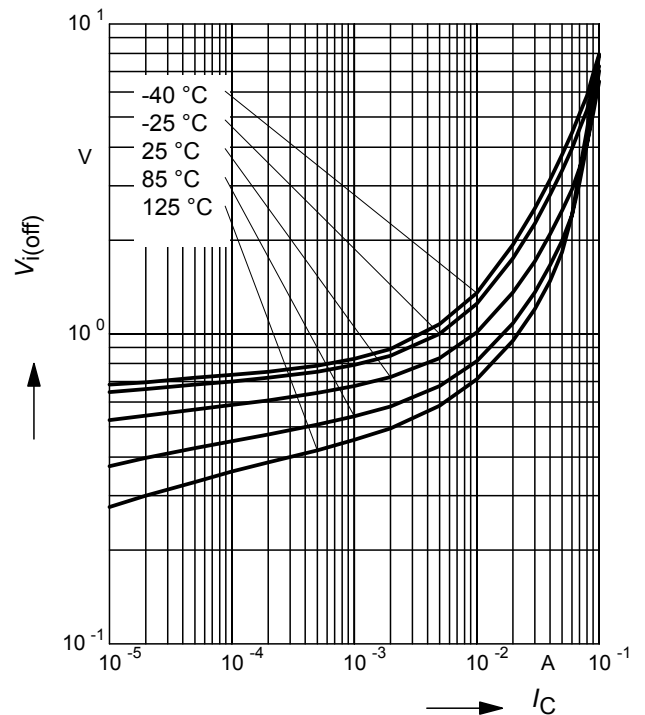
Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R_{thJS}		K/W
BCR129		≤ 240	
BCR129S		≤ 140	
BCR129W		≤ 105	

¹⁾For calculation of R_{thJA} please refer to Application Note AN077 (Thermal Resistance Calculation)


Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage $I_C = 100 \mu\text{A}, I_B = 0$	$V_{(BR)CEO}$	50	-	-	V
Collector-base breakdown voltage $I_C = 10 \mu\text{A}, I_E = 0$	$V_{(BR)CBO}$	50	-	-	
Collector-base cutoff current $V_{CB} = 40 \text{ V}, I_E = 0$	I_{CBO}	-	-	100	nA
Emitter-base cutoff current $V_{EB} = 5 \text{ V}, I_C = 0$	I_{EBO}	-	-	100	nA
DC current gain ¹⁾ $I_C = 5 \text{ mA}, V_{CE} = 5 \text{ V}$	h_{FE}	120	-	630	-
Collector-emitter saturation voltage ¹⁾ $I_C = 10 \text{ mA}, I_B = 0.5 \text{ mA}$	V_{CEsat}	-	-	0.3	V
Input off voltage $I_C = 100 \mu\text{A}, V_{CE} = 5 \text{ V}$	$V_{i(off)}$	0.4	-	1	
Input on voltage $I_C = 2 \text{ mA}, V_{CE} = 0.3 \text{ V}$	$V_{i(on)}$	0.5	-	1.1	
Input resistor	R_1	7	10	13	k Ω
AC Characteristics					
Transition frequency $I_C = 10 \text{ mA}, V_{CE} = 5 \text{ V}, f = 100 \text{ MHz}$	f_T	-	150	-	MHz
Collector-base capacitance $V_{CB} = 10 \text{ V}, f = 1 \text{ MHz}$	C_{cb}	-	3	-	pF

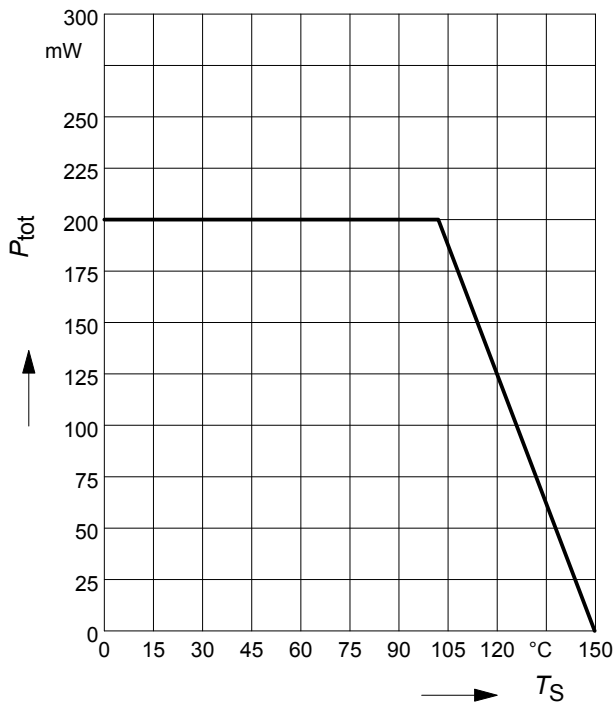
¹Pulse test: $t < 300 \mu\text{s}$; $D < 2\%$

DC current gain $h_{FE} = f(I_C)$ $V_{CE} = 5\text{ V}$ (common emitter configuration)**Collector-emitter saturation voltage** $V_{CEsat} = f(I_C)$, $I_C/I_B = 20$ **Input on Voltage $V_{i(on)} = f(I_C)$** $V_{CE} = 0.3\text{ V}$ (common emitter configuration)**Input off voltage $V_{i(off)} = f(I_C)$** $V_{CE} = 5\text{ V}$ (common emitter configuration)



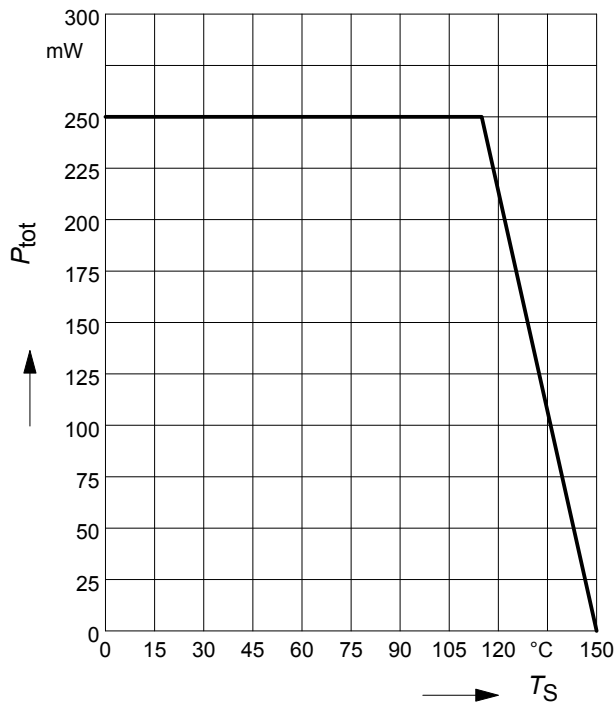
Total power dissipation $P_{tot} = f(T_S)$

BCR129



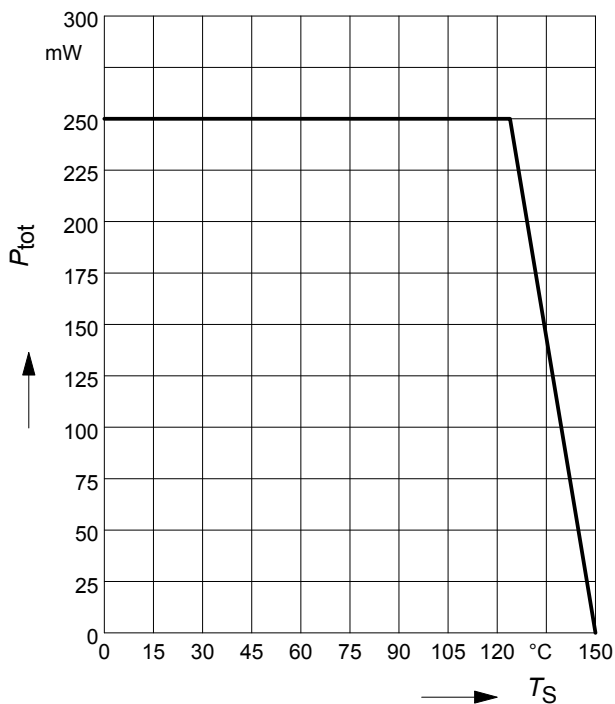
Total power dissipation $P_{tot} = f(T_S)$

BCR129S



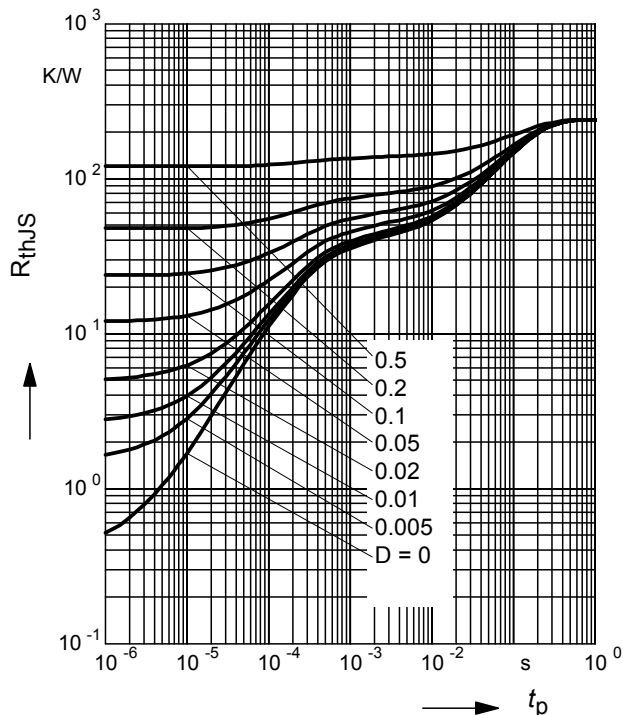
Total power dissipation $P_{tot} = f(T_S)$

BCR129W



Permissible Pulse Load $R_{thJS} = f(t_p)$

BCR129

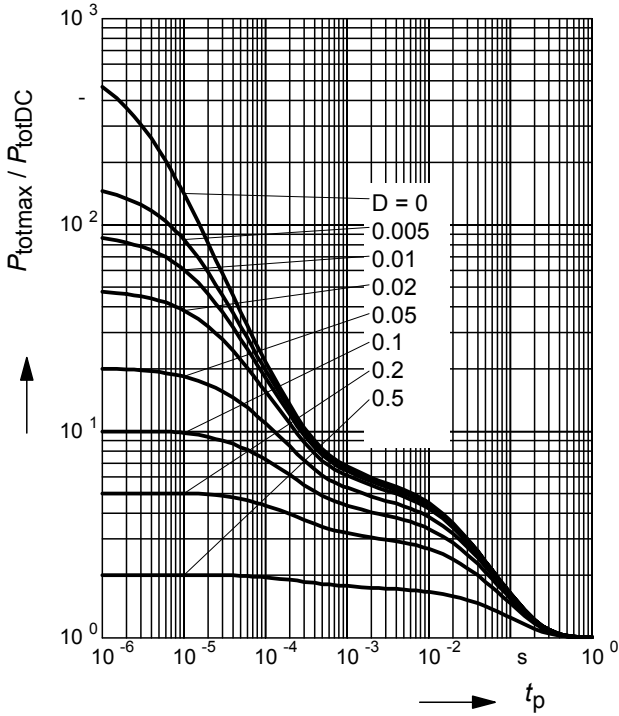




Permissible Pulse Load

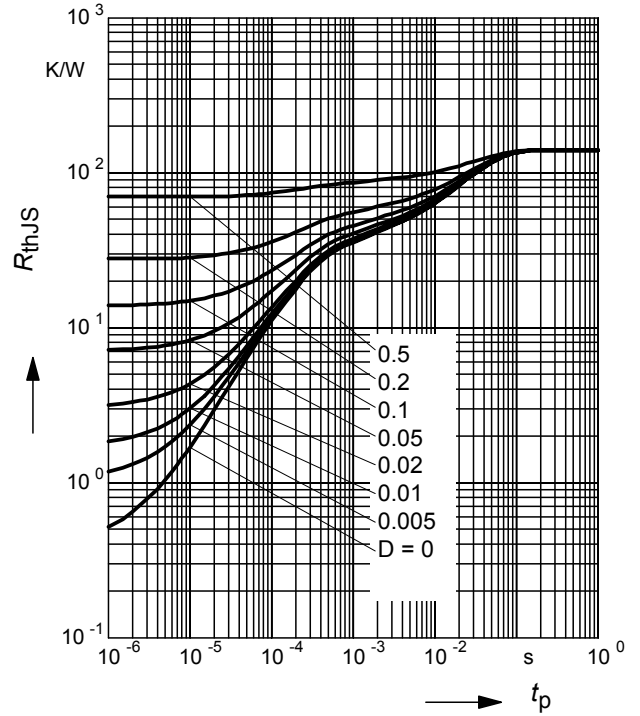
$$P_{\text{totmax}}/P_{\text{totDC}} = f(t_p)$$

BCR129



Permissible Puls Load $R_{\text{thJS}} = f(t_p)$

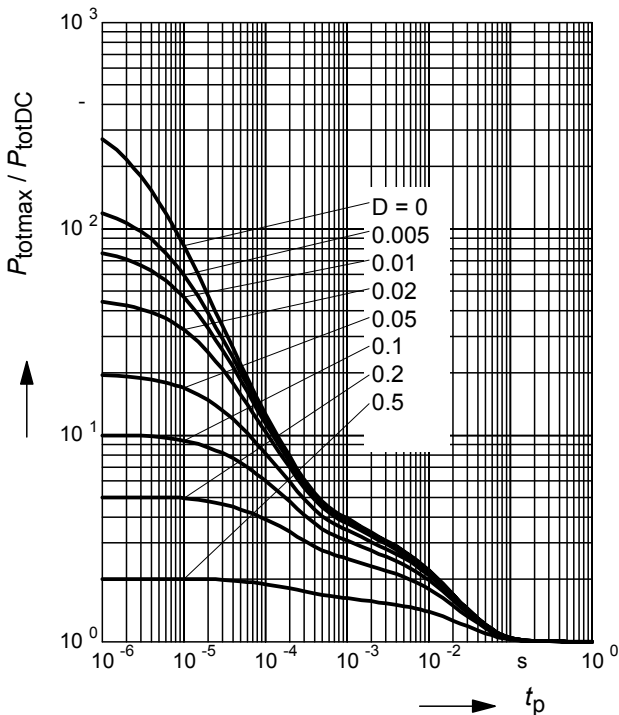
BCR129S



Permissible Pulse Load

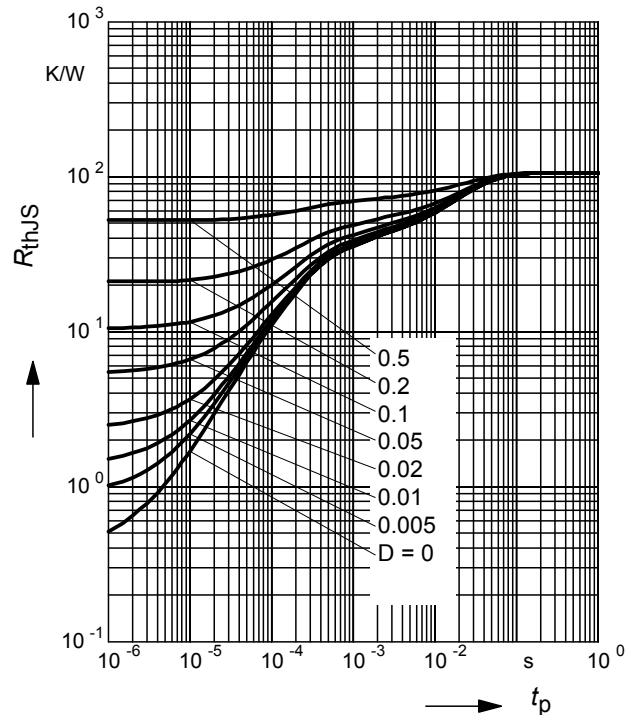
$$P_{\text{totmax}}/P_{\text{totDC}} = f(t_p)$$

BCR129S



Permissible Puls Load $R_{\text{thJS}} = f(t_p)$

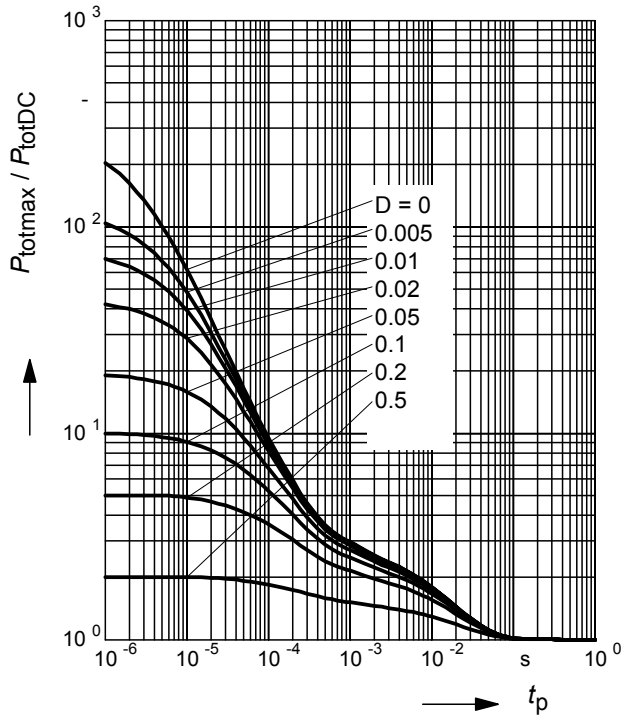
BCR129W



Permissible Pulse Load

$$P_{\text{totmax}}/P_{\text{totDC}} = f(t_p)$$

BCR129W

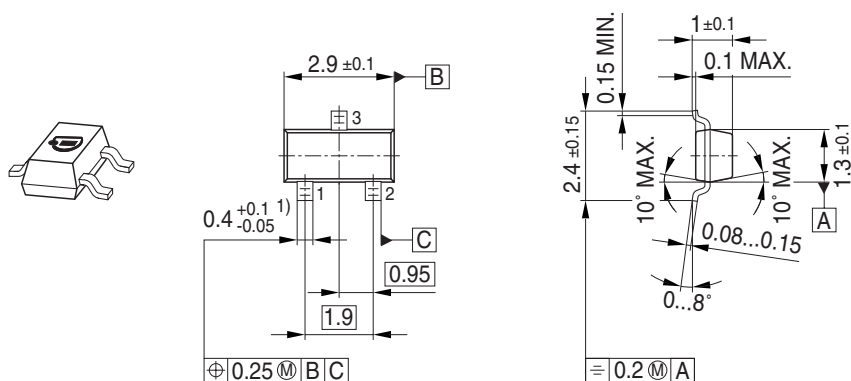




Package SOT23

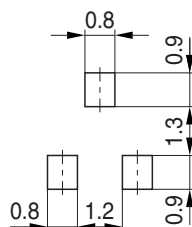
BCR129...

Package Outline

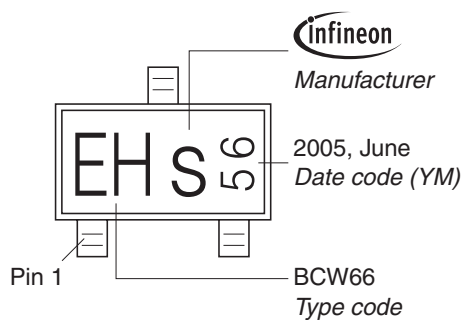


1) Lead width can be 0.6 max. in dambar area

Foot Print

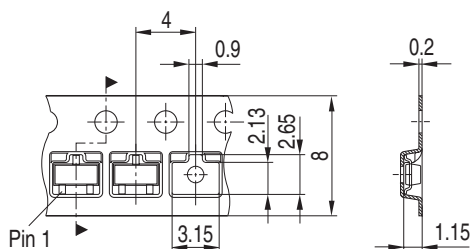


Marking Layout (Example)

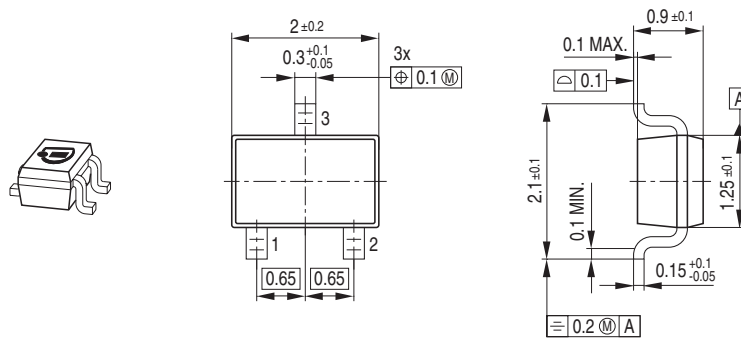


Standard Packing

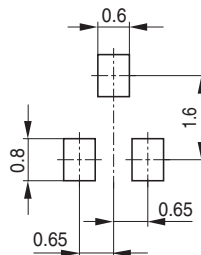
Reel $\phi 180$ mm = 3.000 Pieces/Reel
 Reel $\phi 330$ mm = 10.000 Pieces/Reel



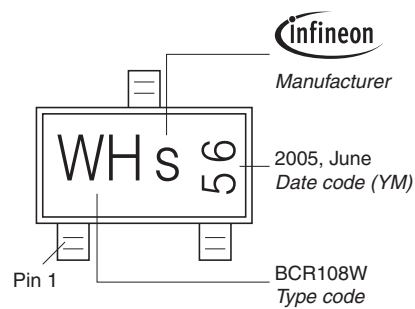
Package Outline



Foot Print

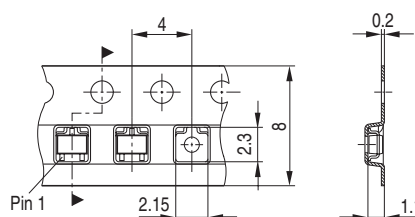


Marking Layout (Example)



Standard Packing

Reel $\varnothing 180$ mm = 3.000 Pieces/Reel
 Reel $\varnothing 330$ mm = 10.000 Pieces/Reel





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